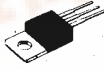
	No.1311	2SC3175
		NPN Epitaxial Planar Type Silicon Transistor FOR CRT HORIZONTAL DEFLECTION OUTPUT

Features:

- High switching speed
- Especially suited for use in high-definition CRT display ($V_{CC}=12$ to $24V$)
- Wide ASO and durable against breakdown

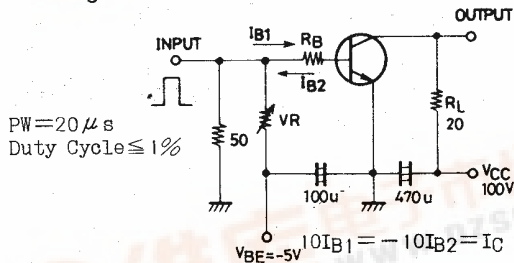
Absolute Maximum Ratings at $T_a=25^\circ C$

			unit
Collector to Base Voltage	V_{CB0}	400	V
Collector to Emitter Voltage	V_{CE0}	200	V
Emitter to Base Voltage	V_{EB0}	6	V
Collector Current	I_C	7	A
Peak Collector Current	i_{cp}	12	A
Base Current	I_B	4	A
Collector Dissipation	P_C $T_c=25^\circ C$	50	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

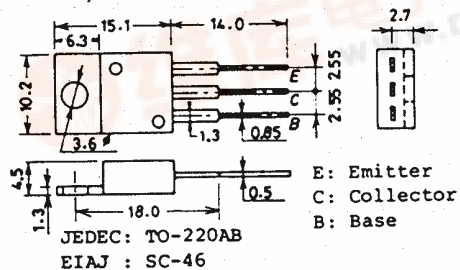
Electrical Characteristics at $T_a=25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=200V, I_E=0$			100	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=5V, I_C=0$			100	μA
DC Current Gain	$h_{FE}(1)$	$V_{CE}=1V, I_C=1A$	15			
	$h_{FE}(2)$	$V_{CE}=1V, I_C=5A$	10		50	
Gain Bandwidth Product	f_T	$V_{CE}=10V, I_C=0.5A$	10	40		MHz
C-E Saturation Voltage	$V_{CE}(sat)$	$I_C=5A, I_B=0.5A$			1	V
B-E Saturation Voltage	$V_{BE}(sat)$	$I_C=5A, I_B=0.5A$			1.2	V
C-B Breakdown Voltage	$V(BR)_{CBO}$	$I_C=1mA, I_E=0$	400			V
C-E Breakdown Voltage	$V(BR)_{CEO}$	$I_C=1mA, R_{BE}=\infty$	200			V
E-B Breakdown Voltage	$V(BR)_{EBO}$	$I_E=1mA, I_C=0$	6			V
Fall Time	t_f	$I_C=5A, I_{B1}=-I_{B2}=0.5A$			0.5	μs

Switching Time Test Circuit



Case Outline 2010A (unit:mm)



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